



DMN63D1L

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	2Ω @ V _{GS} = 10V	380mA
000	3Ω @ V _{GS} = 5V	310mA

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

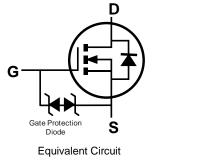
Mechanical Data

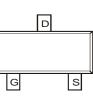
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.008 grams (Approximate)



Top View

SOT23





Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN63D1L-7	SOT23	3000/Tape & Reel
DMN63D1L-13	SOT23	10000/Tape & Reel

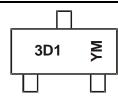
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



3D1 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Notes:

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Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	E	F	G	Н		J	K	L	М
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Duris Courset (Note C) // 401/	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	380 300	mA
Continuous Drain Current (Note 6) $V_{GS} = 10V$	t<5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	430 340	mA
Maximum Continuous Body Diode Forward Curren	t (Note 6)	ls	0.5	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 6)			I _{DM}	1.2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 5)		PD	370	mW	
Thermal Desistance, Junction to Ambient (Nate 5)	Steady State	D	338	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	R _{θJA}	292	C/W	
Total Power Dissipation (Note 6)		PD	560	mW	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Devi	227	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	R _{0JA}	197	C/VV	
Operating and Storage Temperature Range		T _{J.} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

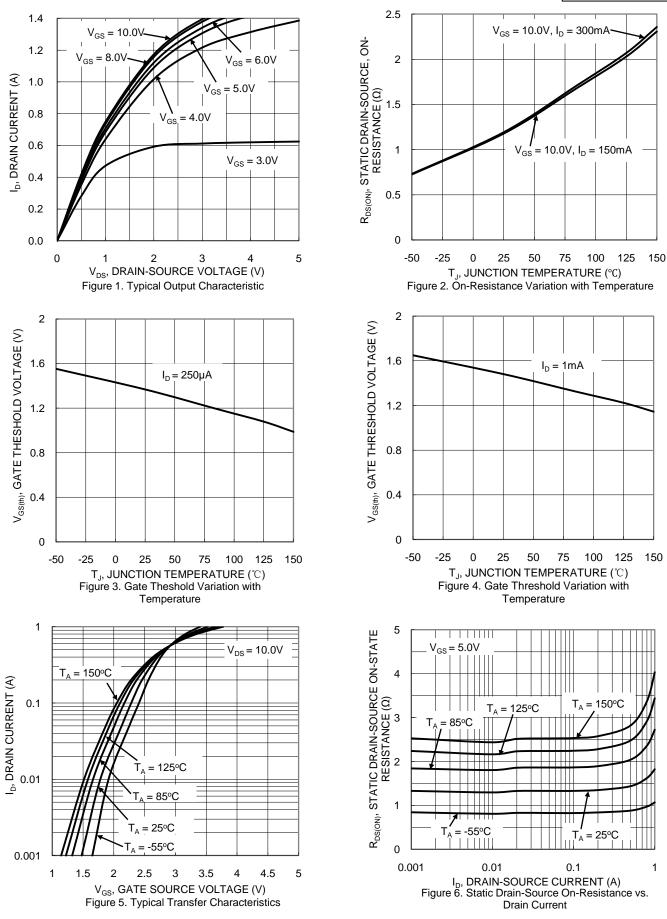
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			71			I.
Drain-Source Breakdown Voltage	BV _{DSS}	60		—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.6	2.5	V	$V_{DS} = 10V, I_D = 1mA$
Static Drain-Source On-Resistance			_	2.0	Ω	$V_{GS} = 10V, I_D = 0.5A$
	R _{DS(ON)}			3.0	12	$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y _{fs}	80	_	—	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V _{SD}		0.75	1.1	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	30	—	pF	
Output Capacitance	C _{oss}		4.2	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss		2.9	—	pF	1 = 1.00012
Gate Resistance	R _g		133	—	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge	Qg		304	_	рС	
Gate-Source Charge	Q _{gs}	_	203	—	рС	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Gate-Drain Charge	Q _{gd}	-	84	—	рС	ID = 23011A
Turn-On Delay Time	t _{D(ON)}	_	3.9	—	ns	
Turn-On Rise Time	t _R	_	3.4	—	ns	$V_{DD} = 30V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OFF)}		15.7	—	ns	$R_{G} = 25\Omega, I_{D} = 200 \text{mA}$
Turn-Off Fall Time	tF	_	9.9	—	ns	1

5. Device mounted on FR-4 PCB, with minimum recommended pad layout. Notes:

Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.



DMN63D1L



NEW PRODUCT

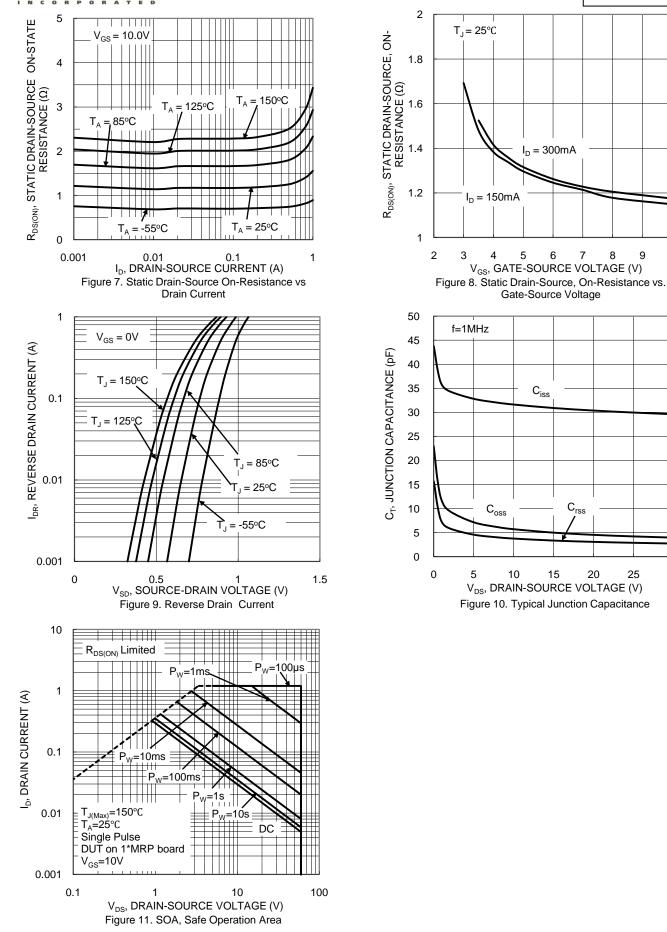
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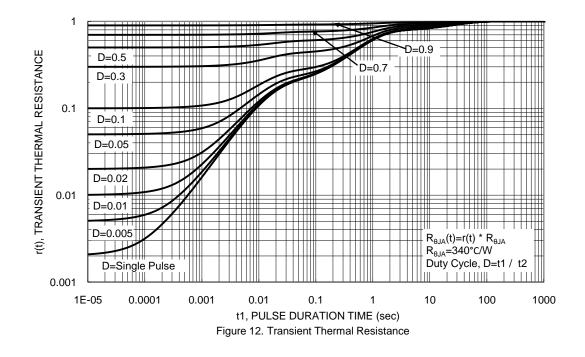
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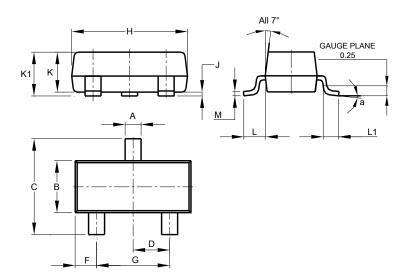
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Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

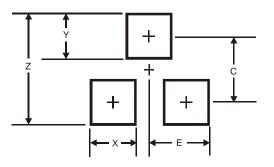


SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
C	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
К	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	8°							
All	All Dimensions in mm							



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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